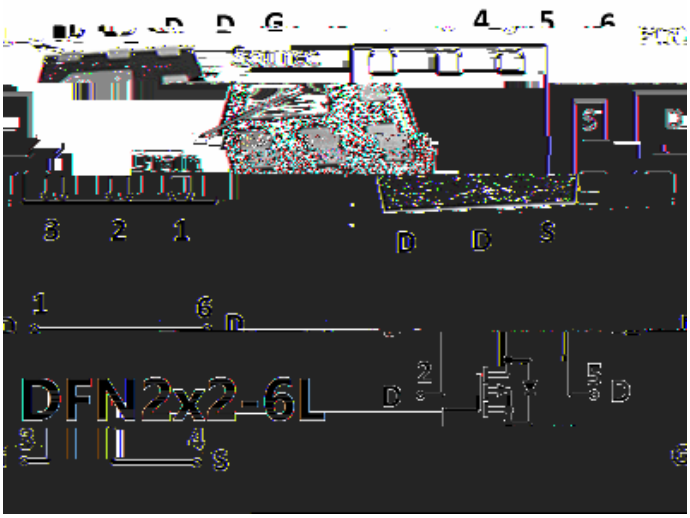
P-Channel Enhancement Mode Field Effect Transistor



Product Summary

- V_{DS} -20V
- I_D -7A
- $R_{DS(ON)}$(at V_{GS}=-4.5V) 36.5mohm
- $R_{DS(ON)}$(at V_{GS}=-2.5V) 46.5mohm
- $R_{DS(ON)}$(at V_{GS}=-1.8V) 60.5mohm

General Description

- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Applications

- Battery protection
- Power management
- Load switch

■ Absolute Maximum Ratings (T_A=25 unless otherwise noted)

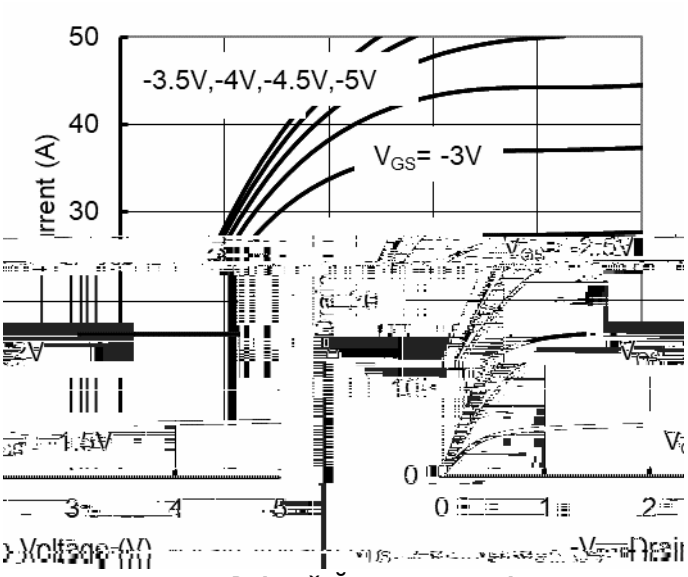
Parameter		Symbol	Maximum	Unit
Drain-source Voltage		V_{DS}	-20	V
Gate-source Voltage		V_{GS}	± 10	V
Drain Current	T_C=25 @ Steady State	I_D	-7	A
	T_C=70 @ Steady State		-5.6	
Pulsed Drain Current [A]		I_{DM}	-28	A
Total Power Dissipation @ T_C=25 [C]		P_D	2.2	W

Thermal Resistance Junction-to-Ambient @ Steady State [D] $R_{\theta JA}$

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJQ4666B	F1	..G66B	3000	30000	120000	7 “ reel

■ **Electrical Characteristics** (T_J=25



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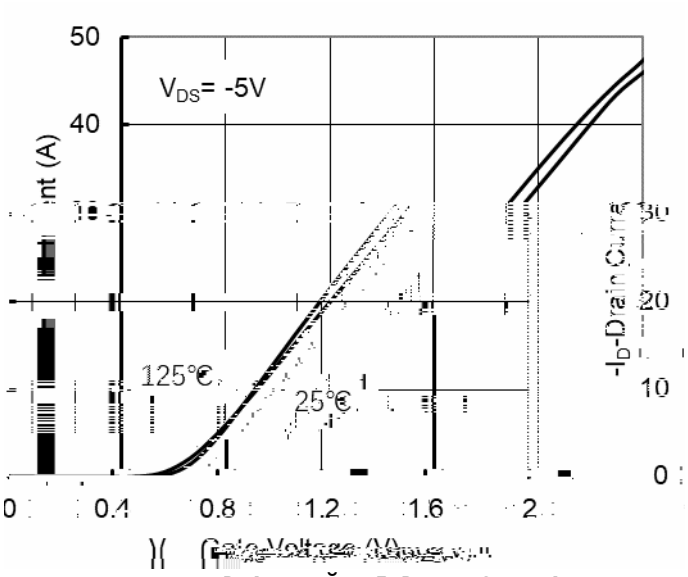

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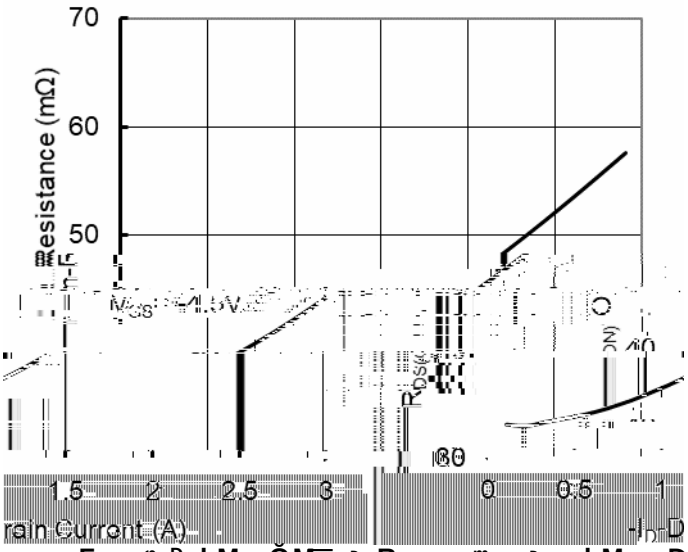
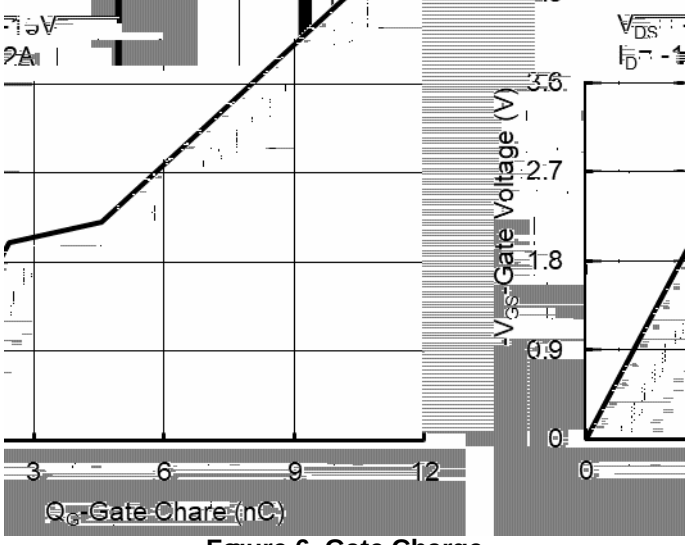


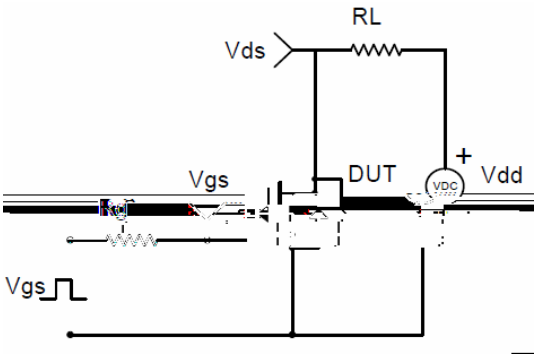
Fc φ D l Mη ŎM¯ ɔ -Resc m ɲ ɔ γ l Mvs. Drain Current and Gate Volta

Fgɐe φ D l MŢ ŎM¯ ɔ -Resc m ɲ ɔ γ l Mvs. Junctc ɔ M ξ

Fɑgure 5. Capacc ɲnce Characterc tc s



Fɑgure 6. Gate Charge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Vds
Vgs
DUT
VDC
+
Vdd
Vgs

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Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instrum w ҿ τ ‘ ‘ rd ndon bquipment b ж rv ʔ pqi ӟ τ lbh ҕ h n2 eq t g nunom i e ӈ